





TRS202E SLLS847F - JULY 2007 - REVISED FEBRUARY 2024

TRS202E 5-V Dual RS-232 Line Driver and Receiver With ±15-kV IEC ESD Protection

1 Features

- IEC61000-4-2 (Level 4) ESD protection for RS-232 bus pins:
 - ±8kV Contact discharge
 - ±15k-V Air-gap discharge
 - ±15kV Human-body model
- Meets or exceeds the requirements of TIA/EIA-232-F and ITU v.28 standards
- Operates at 5V V_{CC} supply
- Operates Up to 120kbit/s
- External capacitors: 4 × 0.1µF or 4 × 1µF
- Latch-up performance exceeds 100mA per JESD 78, class II

2 Applications

- **Battery-powered systems**
- **Notebooks**
- Laptops
- **Set-Top Boxes**
- Hand-held equipment

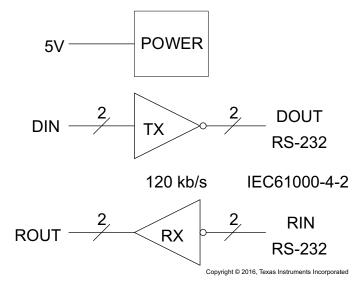
3 Description

The TRS202E consists of two line drivers, two line receivers, and a dual charge-pump circuit. TRS202E has IEC61000-4-2 (Level 4) ESD protection pin-topin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 5V supply. The device operates at data signaling rates up to 120kbit/s and a maximum of 30V/µs driver output slew rate.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
TRS202E	SOIC (D) (16)	9.9mm × 6mm
	SOIC (DW) (16)	10.4mm × 10.3mm
TR3202E	PDIP (N) (16)	19.3mm × 9.4mm
	TSSOP (PW) (16)	5mm x 6.4mm

- For more Information, see Section 10.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Logic Diagram (Positive Logic)



Table of Contents

1 Features1	6.2
2 Applications	6.3
3 Description1	6.4
4 Pin Configuration and Functions3	7 App
5 Specifications4	7.1
5.1 Absolute Maximum Ratings4	7.2
5.2 ESD Ratings4	7.3
5.3 Recommended Operating Conditions4	7.4
5.4 Thermal Information5	8 Devi
5.5 Electrical Characteristics5	8.1
5.6 Electrical Characteristics: Driver5	8.2
5.7 Electrical Characteristics: Receiver5	8.3
5.8 Switching Characteristics: Driver6	8.4
5.9 Switching Characteristics: Receiver6	8.5
5.10 Typical Characteristics7	9 Rev
Parameter Measurement Information8	10 Me
6 Detailed Description9	Info
6.1 Overview	

Information	15
10 Mechanical, Packaging, and Orderable	
9 Revision History	14
8.5 Glossary	14
8.4 Electrostatic Discharge Caution	
8.3 Trademarks	14
8.2 Support Resources	14
8.1 Receiving Notification of Documentation Updates	14
8 Device and Documentation Support	14
7.4 Layout	13
7.3 Power Supply Recommendations	12
7.2 Typical Application	11
7.1 Application Information	11
7 Application and Implementation	
6.4 Device Functional Modes	
6.3 Feature Description	9
6.∠ Functional Block Diagram	9



4 Pin Configuration and Functions

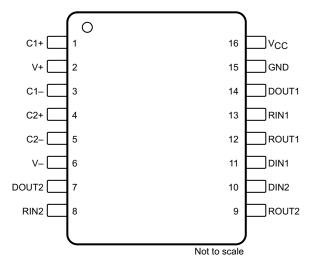


Figure 4-1. D, DW, N or PW Package, 16-Pin SOIC or TSSOP (Top View)

Table 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME	1/0	DESCRIPTION
1	C1+	_	Positive lead of C1 capacitor
2	V+	0	Positive charge pump output for storage capacitor only
3	C1-	_	Negative lead of C1 capacitor
4	C2+	_	Positive lead of C2 capacitor
5	C2-	_	Negative lead of C2 capacitor
6	V-	0	Negative charge pump output for storage capacitor only
7	DOUT2	0	RS-232 line data output (to remote RS-232 system)
8	RIN2	I	RS-232 line data input (from remote RS-232 system)
9	ROUT2	0	Logic data output (to UART)
10	DIN2	I	Logic data input (from UART)
11	DIN1	I	Logic data input (from UART)
12	ROUT1	0	Logic data output (to UART)
13	RIN1	I	RS-232 line data input (from remote RS-232 system)
14	DOUT1	0	RS-232 line data output (to remote RS-232 system)
15	GND	_	Ground
16	V _{CC}	_	Supply voltage, connect to external 5-V power supply



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		МІ	N	MAX	UNIT
Supply voltage, V _{CC} ⁽²⁾		-0	.3	6	V
Positive charge pump voltage, V+(2)		V _{CC} -	- 0.3	14	V
Negative charge pump voltage, V–		-1	4	0.3	V
Input voltage, V _I	Drivers	-0	.3	V+ + 0.3	V
	Receivers			±30] V
Output valtage V	Drivers	V	0.3	V+ + 0.3	V
Output voltage, V _O	Receivers	-0	.3	V _{CC} + 0.3] V
Short-circuit duration, D _{OUT}			Contir	nuous	
Operating virtual junction temperature, T _J				150	°C
Storage temperature, T _{stg}		-6	5	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to network GND.

5.2 ESD Ratings

				VALUE	UNIT
V _(ESD) Electr		Human-body model (HBM),	Pins 7, 8, 13, 14, 15	±15000	
		per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All other pins	±2000	
	Charged-device model (CDM), per JEDEC specification JESD22-0 IEC 61000-4-2 contact discharge IEC 61000-4-2 air-gap discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	All pins	±1500	V
		IEC 61000-4-2 contact discharge	Pins 7, 8, 13, 14, 15	±8000	
		IEC 61000-4-2 air-gap discharge	Pins 7, 8, 13, 14, 15	±15000	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

see Figure 7-1 (1)

			MIN	NOM	MAX	UNIT
	Supply voltage		4.5	5	5.5	V
V _{IH}	Driver high-level input voltage (D _{IN})		2			V
V _{IL}	Driver low-level input voltage (D _{IN})				0.8	V
Vı	Driver input voltage (D _{IN})				5.5	V
V _I	Receiver input voltage				30	
T _A	Operating free-air temperature	TRS202EC	0		70	°C
		TRS202EI	-40		85	

(1) Test conditions are C1 to C4 = $0.1\mu F$ at V_{CC} = 5V $\pm 0.5 V$.

Submit Document Feedback



5.4 Thermal Information

THERMAL METRIC(1)		D (SOIC)	DW (SOIC)	N (PDIP)	PW (TSSOP)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	84.6	77.1	44.1	107.5	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	43.5	39.9	30.8	38.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.2	41.8	24.2	53.7	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	10.4	12.9	15.2	3.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	42.8	41.3	24	53.1	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see Figure 7-1)(1)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
I _{CC} Supply current	No load, V _{CC} = 5V		8	15	mA

- (1) Test conditions are C1 to C4 = 0.1μ F at V_{CC} = 5V + 0.5V.
- (2) All typical values are at $V_{CC} = 5V$ and $T_A = 25$ °C.

5.6 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 7-1)(1)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	D_{OUT} at $R_L = 3k\Omega$ to GND, $D_{IN} = GND$	5	9		V
V _{OL}	Low-level output voltage	D_{OUT} at $R_L = 3k\Omega$ to GND, $D_{IN} = V_{CC}$	-5	-9		V
I _{IH}	High-level input current	V _I = V _{CC}		15	200	μA
I _{IL}	Low-level input current	V _I at 0V		-15	-200	μA
I _{OS} (3)	Short-circuit output current	V_{CC} = 5.5V and V_{O} = 0V		±10	±60	mA
r _o	Output resistance	V_{CC} , V+, V- = 0V, and V_{O} = ±2V	300			Ω

- (1) Test conditions are C1 to C4 = 0.1μ F at V_{CC} = 5V + 0.5V.
- (2) All typical values are at $V_{CC} = 5V$ and $T_A = 25$ °C.
- (3) Short-circuit durations must be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output must be shorted at a time.

5.7 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see Figure 7-1)(1)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1mA	3.5	V _{CC} - 0.4		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6mA			0.4	V
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 5V and T _A = 25°C		1.7	2.4	V
V _{IT} _	Negative-going input threshold voltage	V _{CC} = 5V and T _A = 25°C	0.8	1.2		V
V _{hys}	Input hysteresis (V _{IT+} – V _{IT-})		0.2	0.5	1	V
ri	Input resistance	V _I = ±3V to ±25V	3	5	7	kΩ

- (1) Test conditions are C1 to C4 = $0.1\mu F$ at V_{CC} = 5V + 0.5V.
- (2) All typical values are at $V_{CC} = 5V$ and $T_A = 25$ °C.

Copyright © 2024 Texas Instruments Incorporated



5.8 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see Figure 7-1)(1)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
	Maximum data rate	C_L = 50 to 1000pF, one D_{OUT} switching, and R_L = 3kΩ to 7kΩ (see Figure 6-1)	120			kbit/s
t _{PLH(D)}	Propagation delay time, low- to high- level output	C_L = 2500pF, all drivers loaded, and R_L = $3k\Omega$ (see Figure 6-1)		2		μs
t _{PHL(D)}	Propagation delay time, high- to low-level output	C_L = 2500pF, all drivers loaded, and R_L = $3k\Omega$ (see Figure 6-1)		2		μs
t _{sk(p)}	Pulse skew ⁽³⁾	C_L = 150 to 2500pF and R_L = 3k Ω to 7k Ω (see Figure 6-2)		300		ns
SR(tr)	Slew rate, transition region	C_L = 50 to 1000pF, V_{CC} = 5V, and R_L = 3k Ω to 7k Ω (see Figure 6-1)	3	6	30	V/µs

Test conditions are C1 to C4 = $0.1\mu F$ at V_{CC} = 5V + 0.5V.

5.9 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see Figure 6-3)(1)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
t _{PLH(R)}	Propagation delay time, low- to high-level output	C _L = 150pF		0.5	10	μs
t _{PHL(R)}	Propagation delay time, high- to low-level output	C _L = 150pF		0.5	10	μs
t _{sk(p)}	Pulse skew ⁽³⁾			300		ns

Test conditions are C1 to C4 = 0.1μ F at V_{CC} = 5V + 0.5V.

⁽²⁾

All typical values are at V_{CC} = 5V and T_A = 25°C. Pulse skew is defined as $|t_{PLH}-t_{PHL}|$ of each channel of the same device.

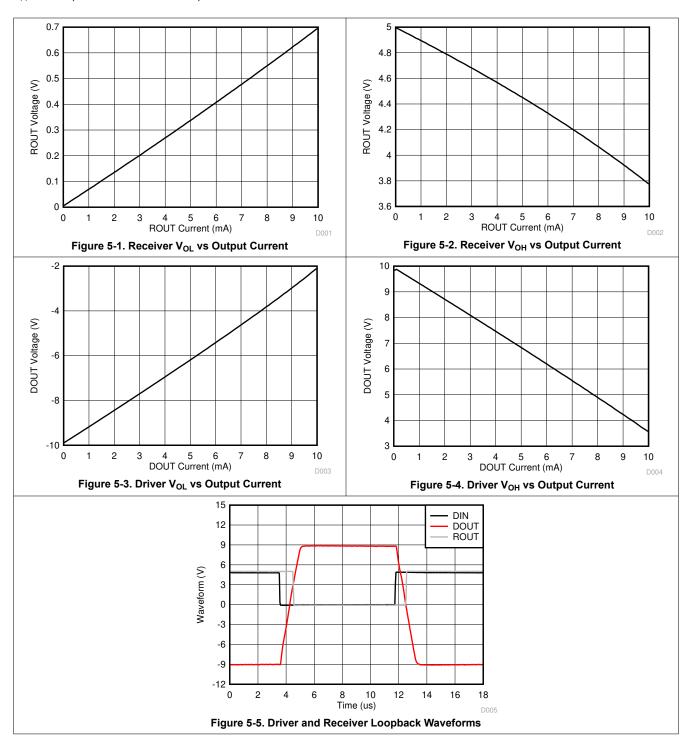
⁽²⁾

All typical values are at V_{CC} = 5V and T_A = 25°C. Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.



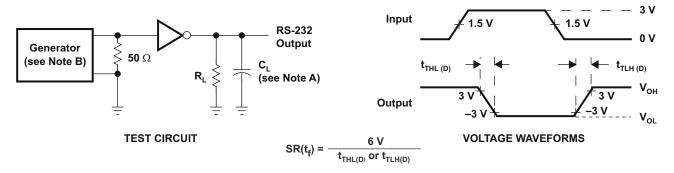
5.10 Typical Characteristics

T_A = 25°C (unless otherwise noted)



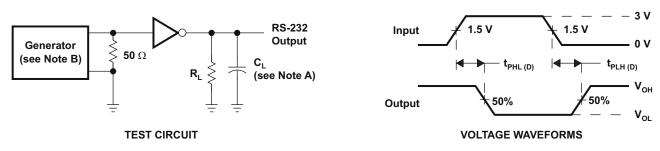


Parameter Measurement Information



- NOTES: A. C_L includes probe and jig capacitance.
 - B. The pulse generator has the following characteristics: PRR = 120 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_f \le 10$ ns.

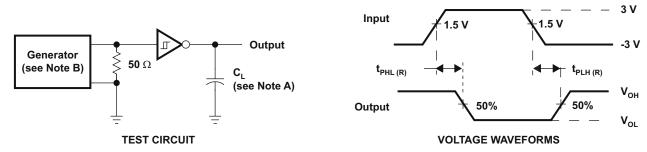
Figure 6-1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 120 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

Figure 6-2. Driver Pulse Skew



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω , 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

Figure 6-3. Receiver Propagation Delay Times

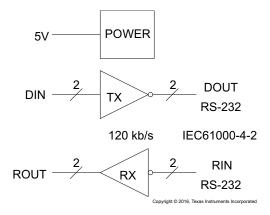


6 Detailed Description

6.1 Overview

The TRS202E device is a dual driver and receiver that includes a capacitive voltage generator using four capacitors to supply TIA/EIA-232-F voltage levels from a single 5V supply. All RS-232 pins have 15kV HBM and IEC61000-4-2 Air-Gap discharge protection. RS-232 pins also have 8-kV IEC61000-4-2 contact discharge protection. Each receiver converts TIA/EIA-232-F inputs to 5V TTL/CMOS levels. These receivers have shorted and open fail safe. The receiver can accept up to ±30V inputs and decode inputs as low as ±3V. Each driver converts TTL/CMOS input levels into TIA/EIA-232-F levels. Outputs are protected against shorts to ground.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Power

The power block increases and inverts the 5V supply for the RS-232 driver using a charge pump that requires four $0.1\mu F$ or $1\mu F$ external capacitors.

6.3.2 RS-232 Driver

Two drivers interface standard logic levels to RS-232 levels. The driver inputs do not have internal pullup resistors. Do not float the driver inputs.

6.3.3 RS-232 Receiver

Two Schmitt trigger receivers interface RS-232 levels to standard logic levels. Each receiver has an internal $5-k\Omega$ load to ground. An open input results in a high output on R_{OUT} .

6.4 Device Functional Modes

6.4.1 V_{CC} Powered by 5V

The device is in normal operation when powered by 5V.

6.4.2 V_{CC} Unpowered

When TRS202E is unpowered, it can be safely connected to an active remote RS-232 device.

Copyright © 2024 Texas Instruments Incorporated

Submit Document Feedback



6.4.3 Truth Tables

Table 6-1 and Table 6-2 list the function for each driver and receiver (respectively).

Table 6-1. Function Table for Each Driver

INPUT DIN ⁽¹⁾	OUTPUT DOUT
L	Н
Н	L

(1) H = high level, L = low level

Table 6-2. Function Table for Each Receiver

INPUT RIN ⁽¹⁾	OUTPUT ROUT
L	Н
Н	L
Open	Н

(1) H = high level, L = low level, Open = input disconnected or connected driver off

7 Application and Implementation

Note

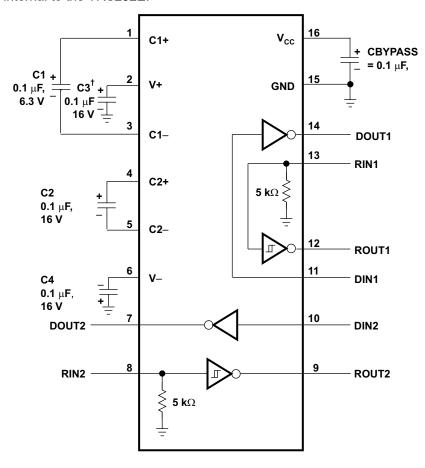
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

For proper operation, add capacitors as shown in Figure 7-1. Pins 9 through 12 connect to UART or general purpose logic lines. RS-232 lines on pins 7, 8, 13, and 14 connect to a connector or cable.

7.2 Typical Application

Two driver and two receiver channels are supported for full duplex transmission with hardware flow control. The two $5k\Omega$ -resistors are internal to the TRS202E.



C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

Copyright © 2016, Texas Instruments Incorporated

Figure 7-1. Typical Operating Circuit and Capacitor Values

B . Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.



7.2.1 Design Requirements

- V_{CC} minimum is 4.5V and maximum is 5.5V.
- Maximum recommended bit rate is 120kbps.

7.2.2 Detailed Design Procedure

7.2.2.1 Capacitor Selection

The capacitor type used for C1 through C4 is not critical for proper operation. The TRS202E requires $0.1\mu F$ capacitors. $1-\mu F$ capacitors are also acceptable. TI recommends ceramic dielectrics. When using the minimum recommended capacitor values, ensure the capacitance value does not degrade excessively as the operating temperature varies. If in doubt, use capacitors with a larger (for example, $2\times$) nominal value. The capacitors' effective series resistance (ESR), which usually rises at low temperatures, influences the amount of ripple on V+ and V-.

Bypass V_{CC} to ground with at least $0.1\mu F$. In applications sensitive to power-supply noise generated by the charge pumps, decouple V_{CC} to ground with a capacitor the same size as (or larger than) the charge-pump capacitors (C1 to C4).

7.2.3 Application Curves

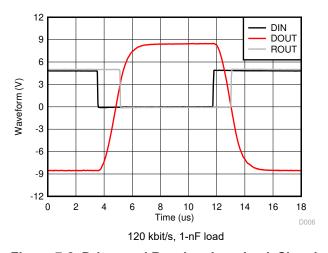


Figure 7-2. Driver and Receiver Loopback Signal

7.3 Power Supply Recommendations

The V_{CC} voltage must be connected to the same power source used for logic device connected to DIN and ROUT pins. V_{CC} must be between 4.5V and 5.5V.

Product Folder Links: TRS202E

Copyright © 2024 Texas Instruments Incorporated



7.4 Layout

7.4.1 Layout Guidelines

Keep the external capacitor traces short. This is more important on C1 and C2 nodes that have the fastest rise and fall times. Make the impedance from TRS202E ground pin and circuit boards ground plane as low as possible for best ESD performance. Use wide metal and multiple vias on both sides of ground pin.

7.4.2 Layout Example

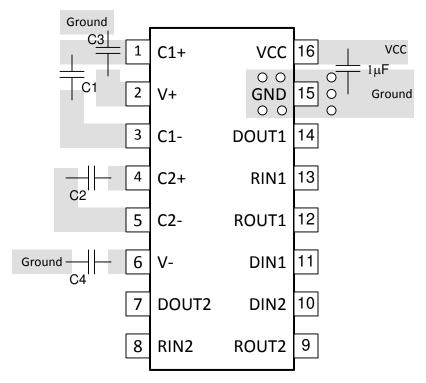


Figure 7-3. TRS202E Layout



8 Device and Documentation Support

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	Changes from Revision E (November 2016) to Revision F (February 2024)	Page
•	Changed the Package Information table	 1
•	Changed the <i>Thermal Information</i> table	
С	Changes from Revision D (November 2012) to Revision E (November 2016)	Page
•	Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	
•	Changed Package thermal impedance, R _{θJA} , values in Thermal Information table From: 73°C/W To: 76.7°C/W (D), From: 57°C/W To: 77.1°C/W (DW), From: 67°C/W To: 44.1°C/W (N), and From: 108°C/W	To:
_	101.7°C/W (PW)	5
С	Changes from Revision C (May 2010) to Revision D (November 2012)	Page
•	Fixed I _{OS} values in <i>Electrical Characteristics</i> table, changed – to ±	5



10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: TRS202E

Copyright © 2024 Texas Instruments Incorporated



www.ti.com 6-Feb-2025

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TRS202ECD	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	0 to 70	TRS202EC	
TRS202ECDR	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	0 to 70	TRS202EC	
TRS202ECDWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS202EC	Samples
TRS202ECN	ACTIVE	PDIP	N	16	25	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	0 to 70	TRS202ECN	Samples
TRS202ECPWR	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	0 to 70	RU02EC	
TRS202EID	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85	TRS202EI	
TRS202EIDR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI	Samples
TRS202EIDW	ACTIVE	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI	Samples
TRS202EIDWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI	Samples
TRS202EIN	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TRS202EIN	Samples
TRS202EIPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RU02EI	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: Til defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

www.ti.com 6-Feb-2025

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com 25-Sep-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRS202ECDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRS202EIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRS202EIDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRS202EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRS202EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



www.ti.com 25-Sep-2024



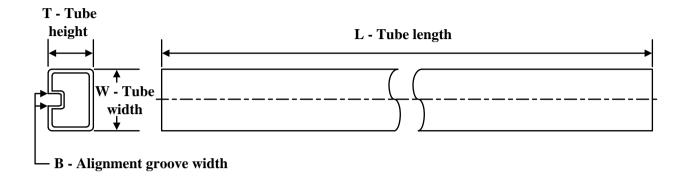
*All dimensions are nominal

7 III dilliciololio die Hollilla							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRS202ECDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRS202EIDR	SOIC	D	16	2500	340.5	336.1	32.0
TRS202EIDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRS202EIPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
TRS202EIPWR	TSSOP	PW	16	2000	353.0	353.0	32.0

PACKAGE MATERIALS INFORMATION

www.ti.com 25-Sep-2024

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TRS202ECN	N	PDIP	16	25	506	13.97	11230	4.32
TRS202EIDW	DW	SOIC	16	40	506.98	12.7	4826	6.6
TRS202EIN	N	PDIP	16	25	506	13.97	11230	4.32

7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated